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Fairchild Semiconductor BCP68

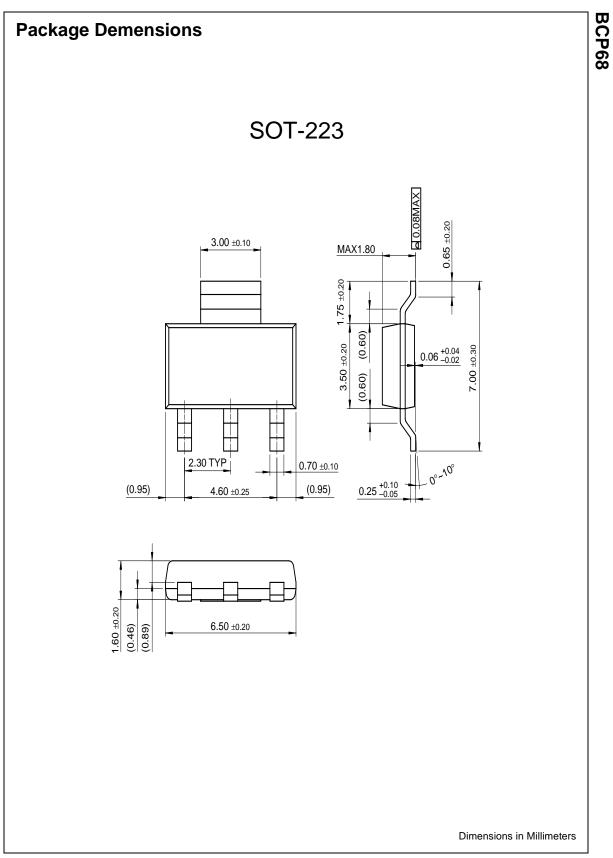
For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



	<b>BCP68</b> <b>NPN General Purpose Amplifier</b> This device is designed for general purpose medium power amplifiers. Sourced from process 37.					4				
	<sup>2</sup> SOT-223 1. Base 2.4. Collector 3. Emitter									
bsolute	Maximum Ratings T <sub>C</sub> =25°C un	less otherwise noted								
Symbol	Parameter			/alue	)	ι	Inits			
V <sub>CEO</sub>	Collector-Emitter Voltage			20			V			
V <sub>CBO</sub>	Collector-Base Voltage			30			V			
V <sub>EBO</sub>	Emitter-Base Voltage			5			V			
c	Collector Current			1			А			
P <sub>D</sub>	Total Device Dissipation @ T - Derate above 25°C	<sub>A</sub> =25°C		1.5 12			Vatts W/°C			
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tem	perature Range	- 55	5 ~ +′	150	°C				
Electrical	Characteristics T <sub>C</sub> =25°C unless	otherwise noted								
Symbol	Characteristics T <sub>C</sub> =25°C unless Parameter ristics	otherwise noted Test Conditions	N	lin.	Тур.	Max.	Units			
Symbol	Parameter			<b>lin.</b> 25	Тур.	Max.	Units			
Symbol Off Characte	Parameter ristics	Test Conditions $I_C = 100\mu A$ , $I_E = 0$ $I_C = 1mA$ , $I_B = 0$			Тур.	Max.				
Symbol Off Characte V <sub>(BR)CES</sub> V <sub>(BR)CEO</sub>	Parameter           ristics           Collector-Emitter Breakdown Voltage           Collector-Emitter Breakdown Voltage           Emitter-Base Breakdown Voltage	I <sub>C</sub> = 100 $\mu$ A, I <sub>E</sub> = 0           I <sub>C</sub> = 1mA, I <sub>B</sub> = 0           I <sub>E</sub> = 10 $\mu$ A, I <sub>C</sub> = 0		25	Тур.	Max.	V			
Symbol Off Characte V <sub>(BR)CES</sub> V <sub>(BR)CEO</sub> V <sub>(BR)EBO</sub>	Parameter ristics Collector-Emitter Breakdown Voltage Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 100 $\mu$ A, I <sub>E</sub> = 0           I <sub>C</sub> = 1mA, I <sub>B</sub> = 0           I <sub>E</sub> = 10 $\mu$ A, I <sub>C</sub> = 0           V <sub>CB</sub> = 25V, I <sub>E</sub> = 0, T <sub>A</sub> = 2	25°C	25 20	Тур.	Max.	V V			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO CBO	Parameter           ristics           Collector-Emitter Breakdown Voltage           Collector-Emitter Breakdown Voltage           Emitter-Base Breakdown Voltage	I <sub>C</sub> = 100 $\mu$ A, I <sub>E</sub> = 0           I <sub>C</sub> = 1mA, I <sub>B</sub> = 0           I <sub>E</sub> = 10 $\mu$ A, I <sub>C</sub> = 0	25°C	25 20	Тур.	10	V V V μΑ			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO On Characte	Parameter         ristics         Collector-Emitter Breakdown Voltage         Collector-Emitter Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector-Base Cutoff Current         Emitter-Base Cutoff Current         ristics (1)	Test Conditions $I_C = 100\mu A, I_E = 0$ $I_C = 1mA, I_B = 0$ $I_E = 10\mu A, I_C = 0$ $V_{CB} = 25V, I_E = 0, T_A = 2$ $V_{CB} = 25V, I_E = 0, T_A = 1$ $V_{EB} = 5V, I_C = 0$	25°C	25 20	Тур.	10 1	V V V μA mA			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO IEBO On Characte	Parameter         ristics       Collector-Emitter Breakdown Voltage         Collector-Emitter Breakdown Voltage       Emitter-Base Breakdown Voltage         Collector-Base Cutoff Current       Emitter-Base Cutoff Current	$\begin{tabular}{ c c c c c } \hline Test Conditions \\ \hline I_C = 100 \mu A, I_E = 0 \\ \hline I_C = 1mA, I_B = 0 \\ \hline I_E = 10 \mu A, I_C = 0 \\ \hline V_{CB} = 25V, I_E = 0, T_A = 2 \\ \hline V_{CB} = 25V, I_E = 0, T_A = 1 \\ \hline V_{EB} = 5V, I_C = 0 \\ \hline \hline I_C = 5mA, V_{CE} = 10V \\ \hline I_C = 500mA, V_{CE} = 1V \\ \hline I_C = 1A, V_{CE} = 1V \\ \hline \hline I_C = 1A, V_{CE} = 1V \\ \hline \hline \hline I_C = 1A, V_{CE} = 1V \\ \hline $	25°C	25 20	Typ.	10 1	V V V μA mA			
Symbol Off Characte V(BR)CES V(BR)CEO V(BR)EBO ICBO ICBO On Characte	Parameter         ristics         Collector-Emitter Breakdown Voltage         Collector-Emitter Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector-Base Cutoff Current         Emitter-Base Cutoff Current         ristics (1)	Test Conditions $I_C = 100\mu A, I_E = 0$ $I_C = 1mA, I_B = 0$ $I_E = 10\mu A, I_C = 0$ $V_{CB} = 25V, I_E = 0, T_A = 2$ $V_{CB} = 25V, I_E = 0, T_A = 1$ $V_{EB} = 5V, I_C = 0$ I_C = 5mA, V_{CE} = 10V $I_C = 500mA, V_{CE} = 1V$	25°C	25 20 5 50 35	Typ.	10 1 10	V V V μA mA			

BCP68





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